

NCE Automotive N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

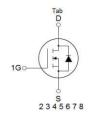
- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =100V, I_D =330A $R_{DS(ON)}$ =1.5m Ω , typical @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ∆Vds tested
- AEC-Q101 qualified







Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP020N10LL	NCEAP020N10LL	TOLL-8L	Ø330mm	24mm	2000 units

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _G s	±20	V	
Drain Current-Continuous	I _D	330	А	
Drain Current-Continuous	I _D (T _C =100°C)	240	А	
Pulsed Drain Current ^(Note 1)	I _{DM}	1320	А	
Maximum Power Dissipation	P _D	400	W	
Derating factor		2.67	W/℃	
Single pulse avalanche energy (Note 4)	E _{AS}	2975	mJ	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	°C	

Thermal Characteristic

Parameter	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Case	Rejc	0.2	0.38	°C/W



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 2)				•	•	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	1.5	2.0	mΩ
Gate resistance	R _G	F=1.0MHz	0.2	2.8	4.0	Ω
Forward Transconductance	G FS	V _{DS} =5V,I _D =165A		200	-	S
Dynamic Characteristics (Note3)	,		•			
Input Capacitance	C _{lss}	\/ F0\/\\ 0\/	-	17000	22100	PF
Output Capacitance	Coss	$V_{DS}=50V, V_{GS}=0V,$	-	1500	1950	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	77	155	PF
Switching Characteristics (Note 3)	,		•			
Turn-on Delay Time	t _{d(on)}		-	37	-	nS
Turn-on Rise Time	t _r	V_{DD} =50 V , I_D =20 A	-	29	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	82	-	nS
Turn-Off Fall Time	t _f		-	34	-	nS
Total Gate Charge	Qg	V 50VI 00A	-	252	327.5	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=50V,I_{D}=20A,$	-	72	93.5	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	63	82	nC
Drain-Source Diode Characteristics	'		1		<u>. </u>	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	330	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = 20A$	-	105	210	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note2)}$	_	290	580	nC

Notes:

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature.

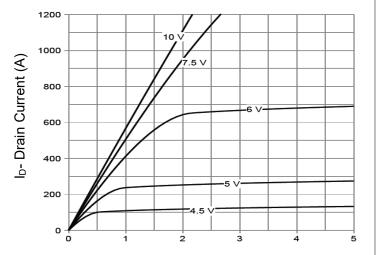
^{2.} The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.

^{3.} Guaranteed by design, not subject to production

^{4.} EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

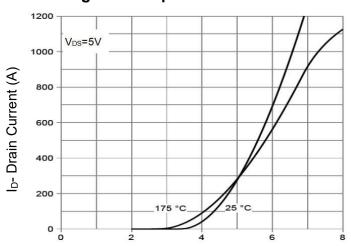


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

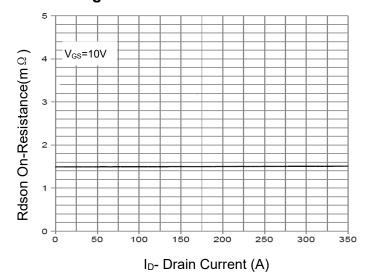
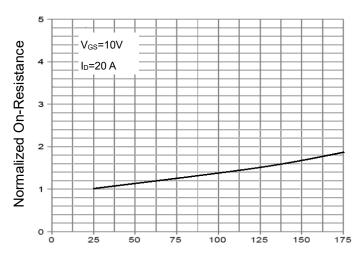
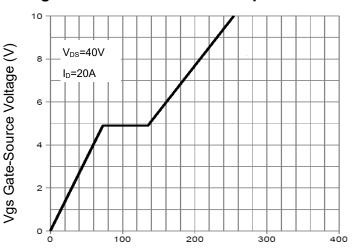


Figure 3 Rdson- Drain Current

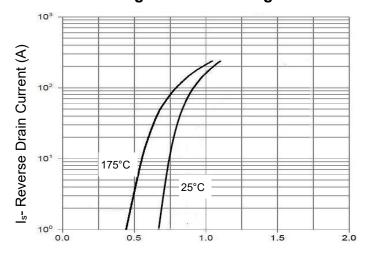


T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



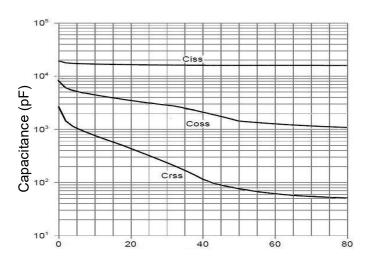
Qg Gate Charge (nC) Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

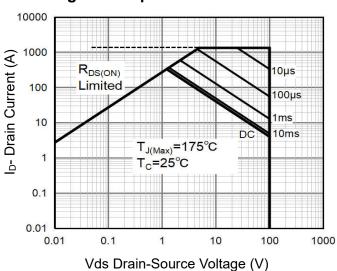
Figure 6 Source- Drain Diode Forward

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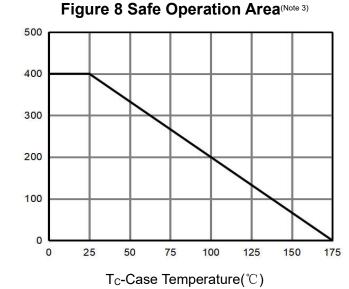


Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds

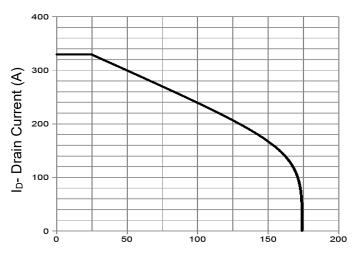


vao Brain Coareo Voltago (V)



Power Dissipation (W)

Figure 9 Power De-rating



T_C-Case Temperature (°C)

Figure 10 Current De-rating

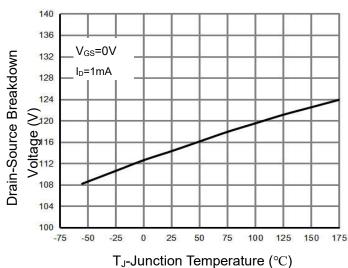


Figure 11 BV_{DSS}-Junction Temperature

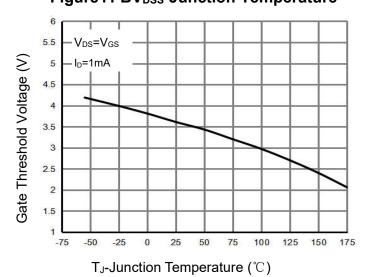
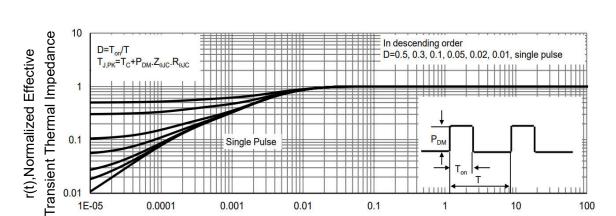


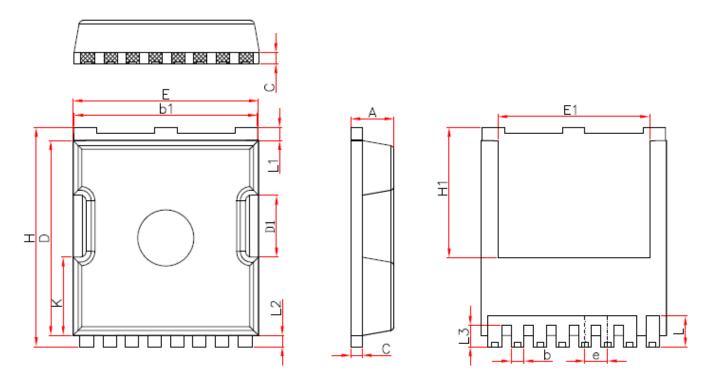
Figure 12 V_{GS(th)}-Junction Temperature



Square Wave Pluse Duration(sec)

Figure 13 Normalized Maximum Transient Thermal Impedance

TOLL-8L Package Information



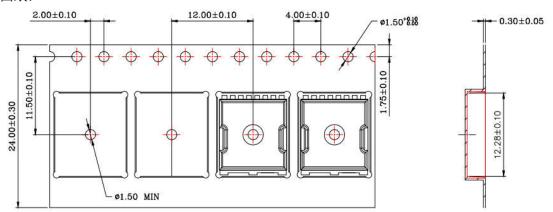
Symbol	Millimeters				
838	Min.	Nom.	Max.		
A	2.20	2.30	2.40		
b	0.65	0.75	0.85		
b1	9.70	9.80	9.90		
C	0.50	0.60	0.70		
D	10.30	10.40	10.50		
D1	3.15	3.3	3.45		
Е	9.70	9.90	10.10		
E1	8.00	8.10	8.20		
е	1.10	1.20	1.30		
Н	11.6	11.7	11.8		
H1	6.85	6.95	7.05		
K	4.08	4.18	4.28		
L	1.60	1.65	2.10		
L1	0.60	0.70	0.80		
L2	0.50	0.60	0.70		
L3	1.05	1.20	1.30		

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-10.50±0.10

Package information

一、载带图纸:



Notes:

- 1. All dimensions are in mm.
- 2. Material: Black Conductive Polystyrene Alloy
- 3. 10 sprocket hole pitch cumulative tolerance ± 0.20 mm .
- 4. Carrier camber is within 1 mm in 250 mm.
- 5. Packing length per 19" reel: 196.0 Meters.
- 6. There must not be foreign body adhesion and the state of the surface must be excellent.
- 7.Surface Resistance 1X10E5~1x10E11 OHMS/SQ

二、包装信息表 (满箱信息)

封装形式	包装方式	盘尺寸	只/盘	盘/内盒	只/内盒	内盒/箱	只/箱
TOLL	编带	13寸	2000	1	2000	8	16000

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